Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	12	adhes$3 near metal$3 near (layer film) near2 (die chip)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/11 15:10
L7	29895	(die chip) near2 (Si silicon "SiO.sub.2" "Si.sub.3N.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/11 15:44
L8	79	7 and (adhes$3 near metal$3 near (layer film))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/11 16:12
L9	2443	(die chip) near2 (surface front back rear) near2 (Si silicon "SiO.sub.2" "Si.sub.3N.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/11 15:59
L10	10	9 and (adhes$3 near metal$3 near (layer film))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/11 15:57
L11	0	(die chip) near2 (surface front back rear) near2 (Si silicon "SiO.sub.2" "Si.sub.3N.sub.4") near2 (adhes$3 near metal$3 near (layer film))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/11 15:58
L12	0	(die chip) near2 (surface front back rear) near2 (Si silicon "SiO.sub.2" "Si.sub.3N.sub.4") with (adhes$3 near metal$3 near (layer film))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/11 15:59
L13	0	(die chip) near2 (surface front back rear) near2 (Si silicon "SiO.sub.2" "Si.sub.3N.sub.4") same (adhes$3 near metal$3 near (layer film))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/11 15:59
L14	395	(die chip) near (surface front back rear) near (Si silicon "SiO.sub.2" "Si.sub.3N.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/11 15:59
L15	0	14 and (adhes$3 near metal$3 near (layer film))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/11 16:00

L16	0	14 and (adhes$3 near metal$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/11 16:00
L17	117	14 and (metal$3 near (layer film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/11 16:01
S70	4	(("6091603") or ("4561011")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/10 13:55
S72	18	(method process$3) AND metal AND adhes$3 AND surface AND (chip die) AND diffus$3 AND (layer film) AND (solder near wet$4) AND substrate AND mount$3 AND solder AND (lid cover) AND adjacent AND material AND apply$3.CLM.	US-PGPUB; USPAT	OR	ON	2006/01/10 14:01
S73	27	(method process$3) AND metal$3 AND adhes$3 AND surface AND (chip die) AND diffus$3 AND (layer film) AND (solder near wet$5) AND substrate AND mount$3 AND solder AND (lid cover) AND adjacent AND material AND apply$3.CLM.	US-PGPUB; USPAT	OR	ON	2006/01/10 14:03
S74	25	(method process$3) AND metal$3 AND adhes$3 AND surface AND (chip die) AND diffus$3 AND (layer film) AND (solder near wet$5) AND substrate AND mount$3 AND solder AND (lid cover) AND adjacent AND material AND apply$3 AND melt$3.CLM.	US-PGPUB; USPAT	OR	ON	2006/01/10 14:08
S76	43	(method process$3) AND metal$3 AND adhes$3 AND back AND surface AND (chip die) AND diffus$3 AND (solder near wet$5) AND ((Si silicon) ("SiO.sub.2" (silicon adj (oxide nitride)))).CLM.	US-PGPUB; USPAT	OR	ON	2006/01/10 14:12
S77	10106	438/106,108,117-119,121,122,125,612,613. ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/11 10:50
S78	293	S77 and (solder with (metal near (layer film)) with (surface (die chip)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/11 10:51
S79	178	S78 and (lid cover)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/11 10:51

S80	172	S79 and (die chip)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/01/11 15:06